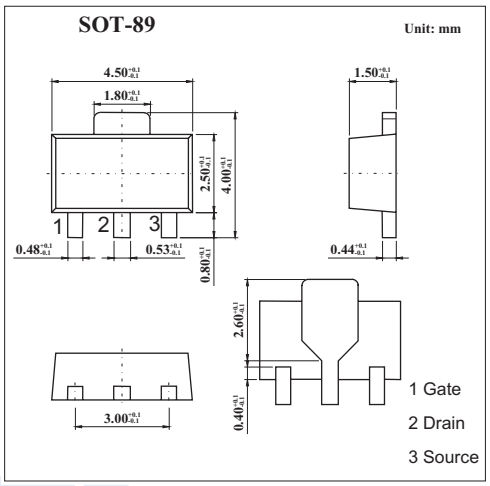
MOS Fied Effect Transistor

2SJ212



Features

- Directly driven by Ics having a 5V poer supply.
- Has low on-state resistance

  $R_{DS(on)}$=4.0Ω MAX.@V_{GS}=-4.0V,I_D=-0.3A

  $R_{DS(on)}$=3.0Ω MAX.@V_{GS}=-1.0V,I_D=-0.5A

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain to source voltage V_{GS}=0	V_{DSS}	-60	V
Gate to source voltage V_{DS}=0	V_{GSS}	±20	V
Drain current (DC)	I_D	±500	m A
Drain current(pulse) *	I_D	±1.0	A
Power dissipation	P_D	2.0	W
Channel temperature	T_{ch}	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* PW ⩽ 10 ms; d ⩾ 50%.

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	V_{DS}=-60V,V_{GS}=0			-10	μA
Gate leakage current	I_{GSS}	V_{GS}=±20V,V_{DS}=0			±10	μA
Gate cut-off voltage	$V_{GS(off)}$	V_{DS}=-10V,I_D=-1mA	-1.0	-2.2	-3.0	V
Forward transfer admittance	|Yfs|	V_{DS}=-5.0V,I_D=-0.3A	0.4	0.54		s
Drain to source on-state resistance	$R_{DS(on)}$	V_{GS}=-4.0V,I_D=-0.3A		1.5	4.0	Ω
		V_{GS}=-10V,I_D=-0.5A		0.8	3.0	Ω
Input capacitance	C_{iss}	V_{DS}=-5.0V,V_{GS}=0,f=1MHZ		160		pF
Output capacitance	C_{oss}			100		pF
Reverse transfer capacitance	C_{rss}			25		pF
Turn-on delay time	$t_{d(on)}$	$V_{GS(on)}$=-4V,R_G=10Ω,V_{DD}=-5V,I_D=--0.3A R_L=1.5Ω		130		ns
Rise time	t_r			380		ns
Turn-off delay time	$t_{d(off)}$			95		ns
Fall time	t_f			140		ns

Marking

Marking	PD